

Abstract of the Disclosure:

During the production of integrated semiconductor structures, it is often necessary to differently dope immediately adjacent regions. A method is provided for producing two adjacent regions of a predetermined area in an integrated semiconductor, whereby a first region of the two adjacent regions includes a doping with a lower target concentration than a second region. The predetermined area of a semiconductor blank is doped with a dopant until a concentration of the dopant is obtained that is at least as high as the target concentration of the second region. A protective layer is applied to the second region, and the dopant is out-diffused from the first region until a concentration of dopant is obtained that corresponds to the target concentration of the first region.

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